

TOSHIBA Field Effect Transistor Silicon N, P Channel MOS Type (U-MOSII)

TPC8401

Lithium Ion Secondary Battery Applications
 Portable Equipment Applications
 Notebook PCs

- Low drain-source ON resistance
 : P Channel $R_{DS(ON)} = 27 \text{ m}\Omega$ (typ.)
 N Channel $R_{DS(ON)} = 14 \text{ m}\Omega$ (typ.)
- High forward transfer admittance
 : P Channel $|Y_{fs}| = 7 \text{ S}$ (typ.)
 N Channel $|Y_{fs}| = 8 \text{ S}$ (typ.)
- Low leakage current
 : P Channel $I_{DSS} = -10 \text{ }\mu\text{A}$ ($V_{DS} = -30 \text{ V}$)
 N Channel $I_{DSS} = 10 \text{ }\mu\text{A}$ ($V_{DS} = 30 \text{ V}$)
- Enhancement-mode
 : P Channel $V_{th} = -0.8 \sim -2.0 \text{ V}$ ($V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$)
 N Channel $V_{th} = 0.8 \sim 2.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

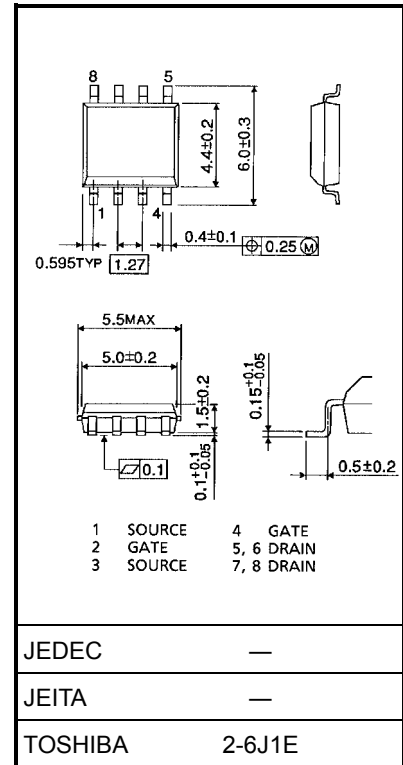
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating		Unit	
		P Channel	N Channel		
Drain-source voltage	V_{DSS}	-30	30	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	-30	30	V	
Gate-source voltage	V_{GSS}	± 20	± 20	V	
Drain current	DC (Note 1)	I_D	-4.5	6	A
	Pulse (Note 1)	I_{DP}	-18	24	
Drain power dissipation ($t = 10\text{s}$) (Note 2a)	Single-device operation (Note 3a)	$P_D(1)$	1.5	1.5	W
	Single-device value at dual operation (Note 3b)	$P_D(2)$	1.0	1.0	
Drain power dissipation ($t = 10\text{s}$) (Note 2b)	Single-device operation (Note 3a)	$P_D(1)$	0.75	0.75	
	Single-device value at dual operation (Note 3b)	$P_D(2)$	0.45	0.45	
Single pulse avalanche energy	E_{AS}	26.3 (Note 4a)	46.8 (Note 4b)	mJ	
Avalanche current	I_{AR}	-4.5	6	A	
Repetitive avalanche energy Single-device value at operation (Note 2a, 3b, 5)	E_{AR}	0.10		mJ	
Channel temperature	T_{ch}	150		$^\circ\text{C}$	
Storage temperature range	T_{stg}	-55~150		$^\circ\text{C}$	

Note: For (Note 1), (Note 2a), (Note 2b), (Note 3a), (Note 3b), (Note 4a), (Note 4b) and (Note 5), please refer to the next page.

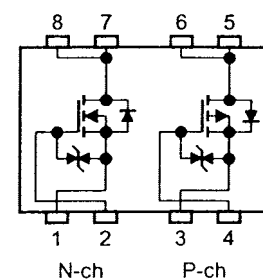
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

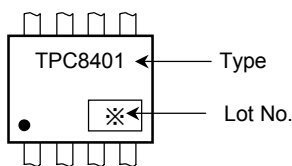
Circuit Configuration



Thermal Characteristics

Characteristics		Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10s)	Single-device operation (Note 3a)	R _{th (ch-a)} (1)	83.3	°C/W
	Single-device value at dual operation (Note 3b)	R _{th (ch-a)} (2)	125	
Thermal resistance, channel to ambient (t = 10s)	Single-device operation (Note 3a)	R _{th (ch-a)} (1)	167	
	Single-device value at dual operation (Note 3b)	R _{th (ch-a)} (2)	278	

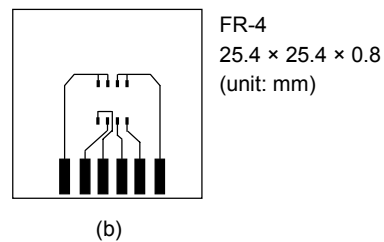
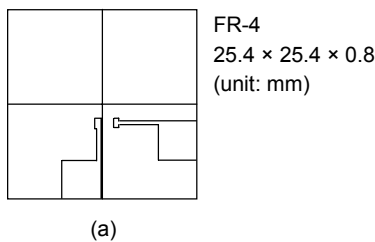
Marking



Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:

- a) Device mounted on a glass-epoxy board (a) b) Device mounted on a glass-epoxy board (b)



Note 3:

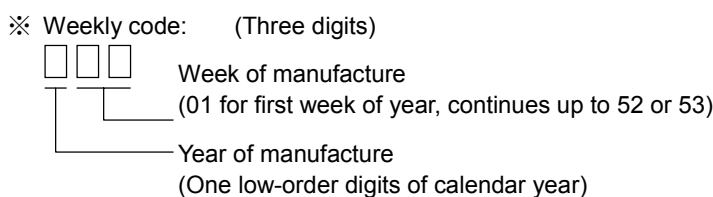
- a) The power dissipation and thermal resistance values are shown for a single device (During single-device operation, power is only applied to one device.)
- b) The power dissipation and thermal resistance values are shown for a single device (During dual operation, power is evenly applied to both devices.)

Note 4:

- a) V_{DD} = -24 V, T_{ch} = 25°C (Initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = -4.5 A
- b) V_{DD} = 24 V, T_{ch} = 25°C (Initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = 6.0 A

Note 5: Repetitive rating: pulse width limited by maximum channel temperature

Note 6: • on lower left of the marking indicates Pin 1.



P-ch

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-15	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4 \text{ V}, I_D = -2.2 \text{ A}$	—	55	65	m Ω
		$R_{DS(ON)}$	$V_{GS} = -10 \text{ V}, I_D = -2.2 \text{ A}$	—	27	35	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -2.2 \text{ A}$	3.5	7	—	S
Input capacitance		C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	970	—	pF
Reverse transfer capacitance		C_{rss}		—	180	—	
Output capacitance		C_{oss}		—	370	—	
Switching time	Rise time	t_r	<p> V_{GS} 0 V -10 V $I_D = -2.2 \text{ A}$ V_{OUT} $R_L = 6.8 \Omega$ $V_{DD} = -15 \text{ V}$ $\text{Duty} \leq 1\%, t_w = 10 \mu\text{s}$ </p>	—	17	—	ns
	Turn-ON time	t_{on}		—	20	—	
	Fall time	t_f		—	75	—	
	Turn-OFF time	t_{off}		—	160	—	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx -24 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -4.5 \text{ A}$	—	28	—	nC
Gate-source charge 1		Q_{gs1}		—	6	—	
Gate-drain ("miller") charge		Q_{gd}		—	12	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	-18	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = -4.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

N-ch

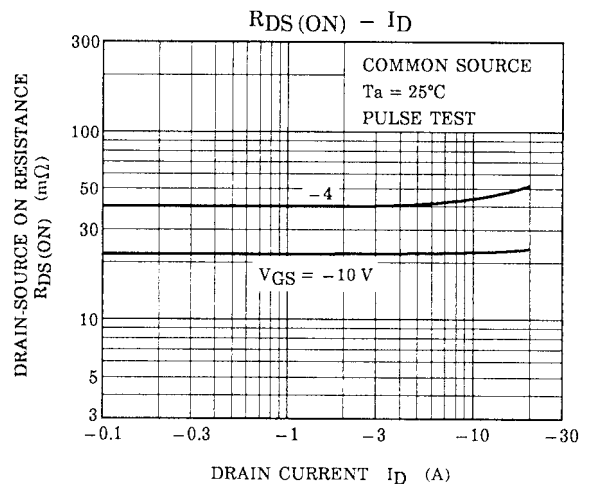
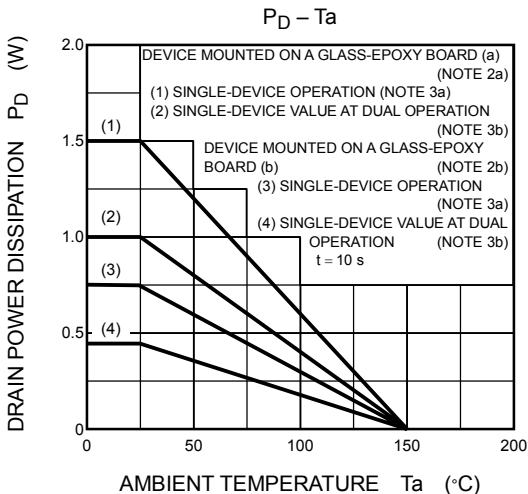
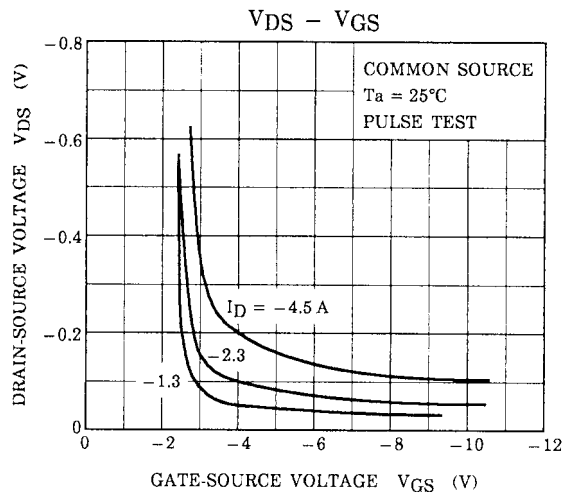
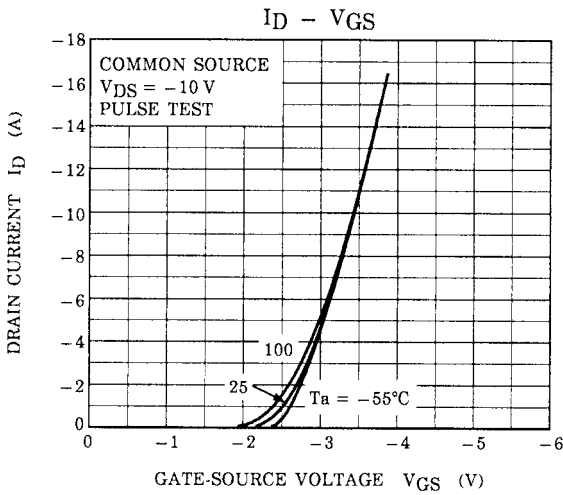
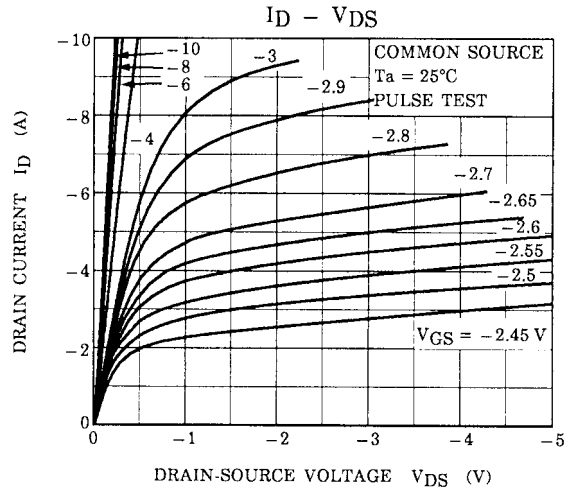
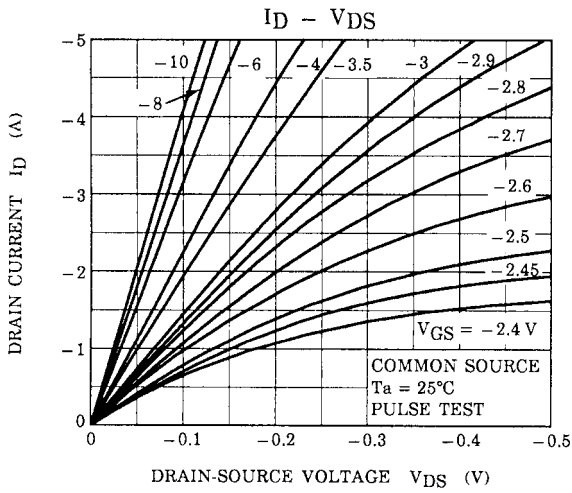
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	30	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	15	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.8	—	2.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 3\text{ A}$	—	21	32	m Ω
		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$	—	14	21	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 3\text{ A}$	4	8	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1700	—	pF
Reverse transfer capacitance		C_{rss}		—	260	—	
Output capacitance		C_{oss}		—	380	—	
Switching time	Rise time	t_r	<p> $V_{GS} = 10\text{ V}, 0\text{ V}$ $I_D = 3.0\text{ A}$ V_{OUT} $R_L = 5.0\ \Omega$ $V_{DD} \approx 15\text{ V}$ $Duty \leq 1\%, t_w = 10\ \mu s$ </p>	—	10	—	ns
	Turn-ON time	t_{on}		—	20	—	
	Fall time	t_f		—	35	—	
	Turn-OFF time	t_{off}		—	120	—	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 6\text{ A}$	—	40	—	nC
Gate-source charge 1		Q_{gs1}		—	28	—	
Gate-drain ("miller") charge		Q_{gd}		—	12	—	

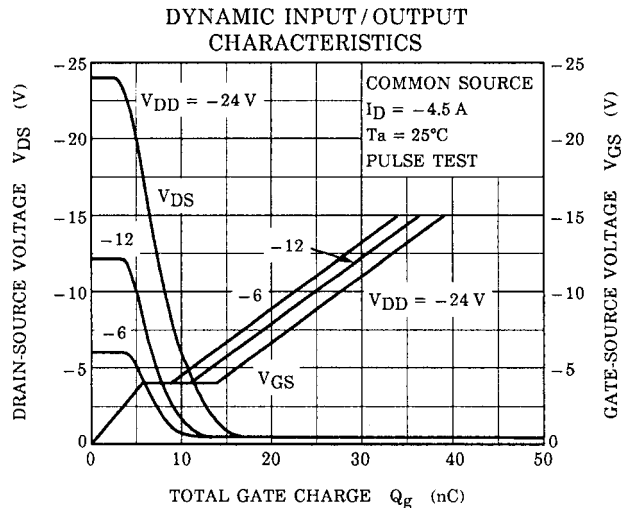
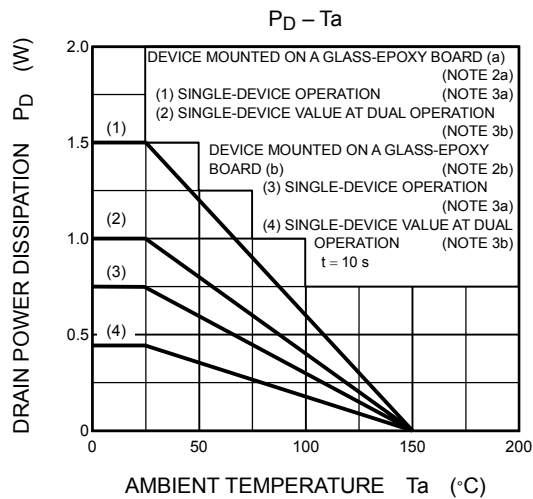
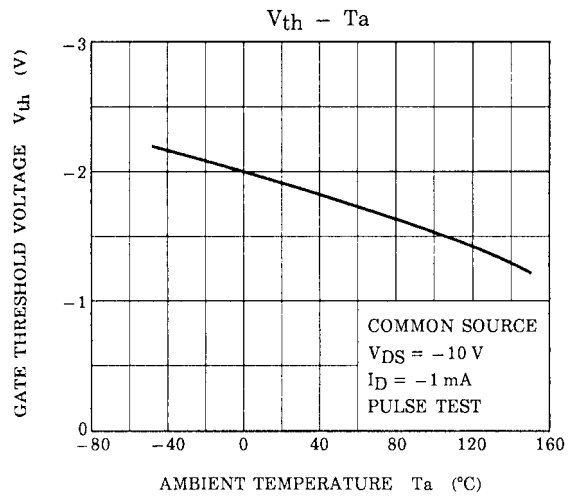
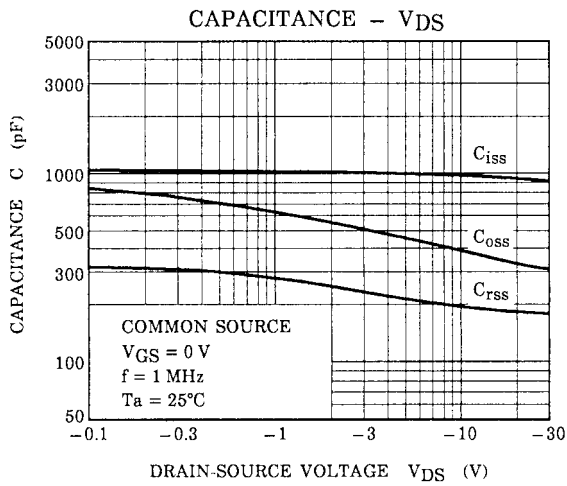
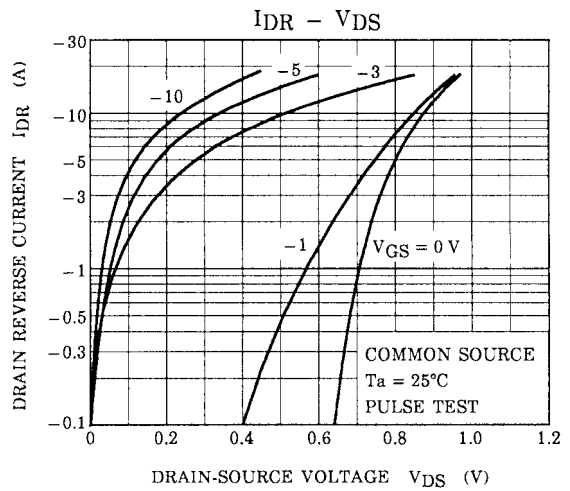
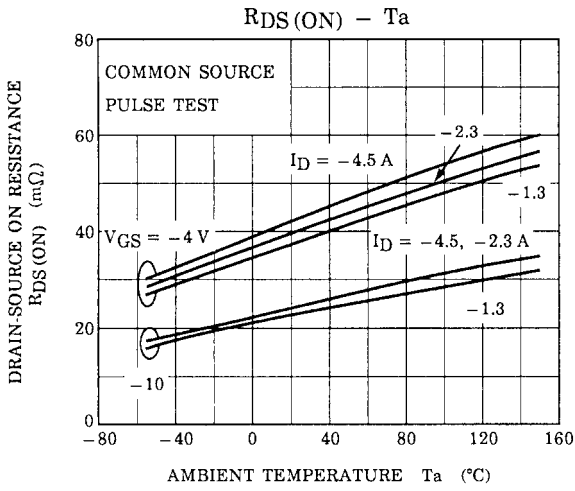
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	24	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 6\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V

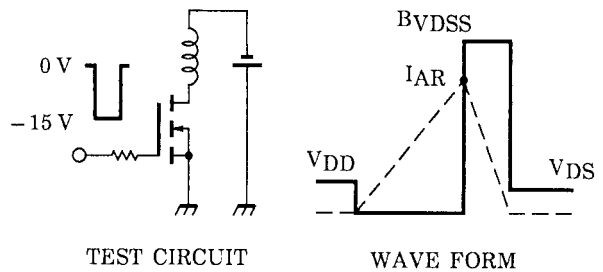
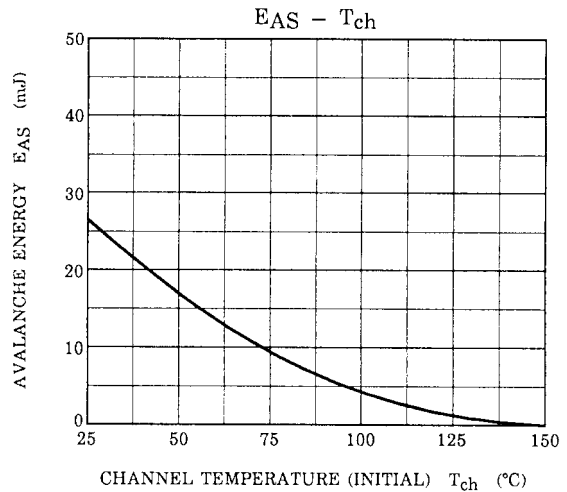
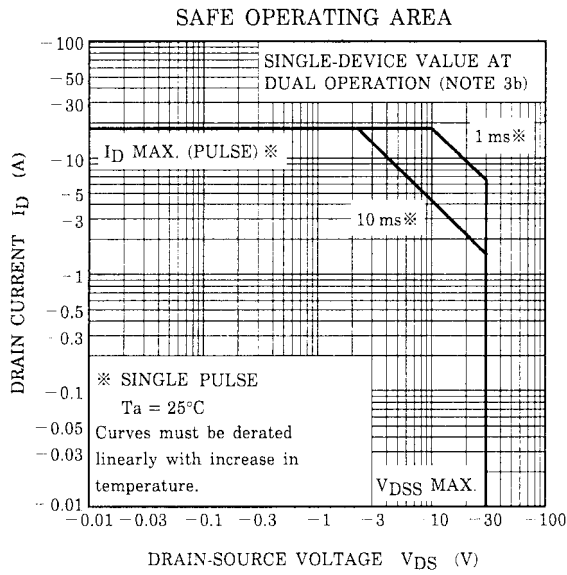
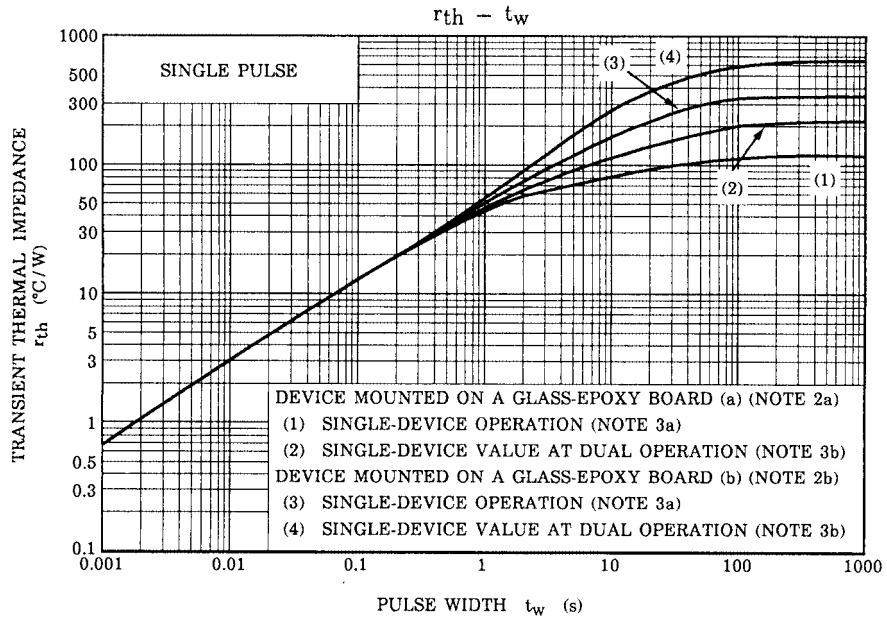
P-ch



P-ch

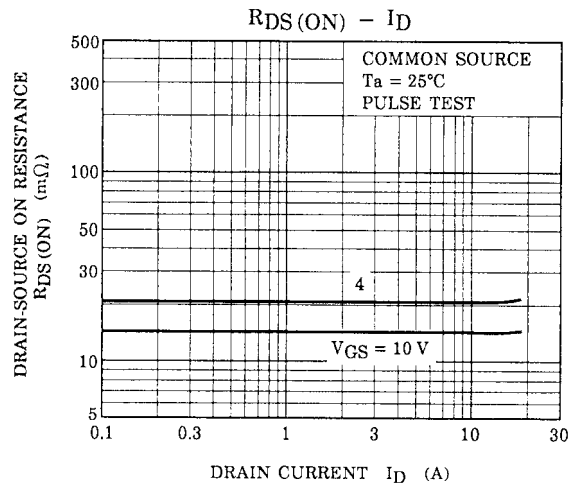
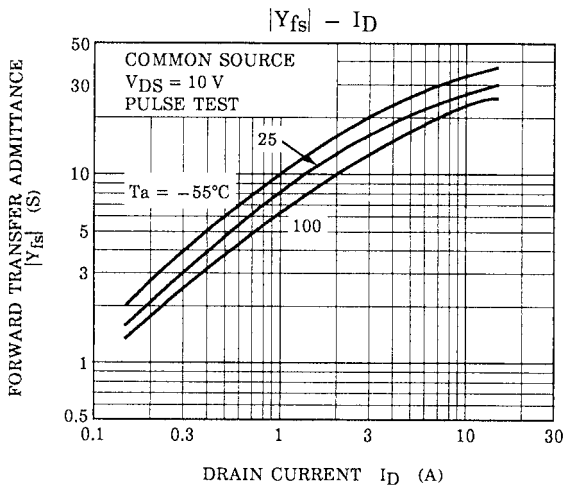
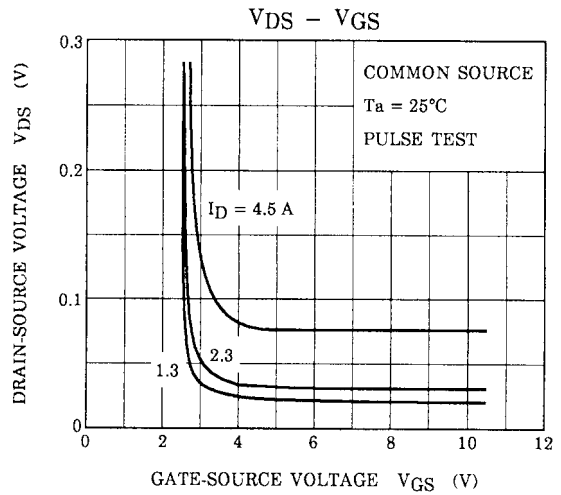
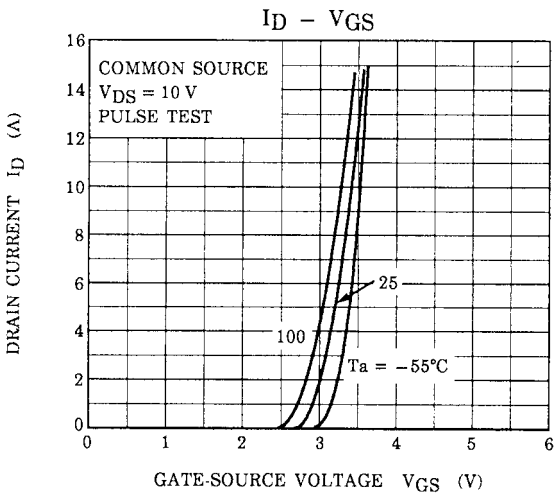
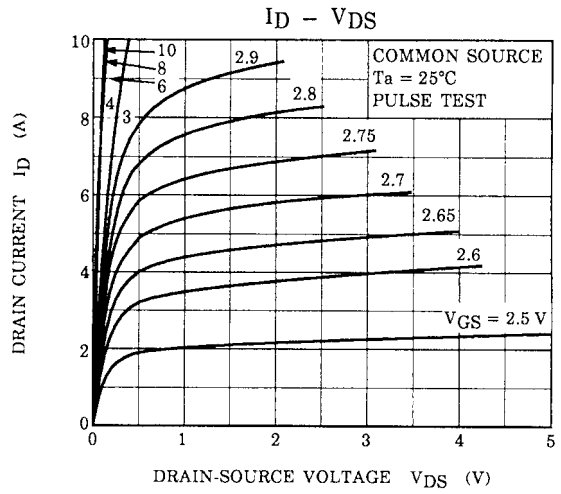
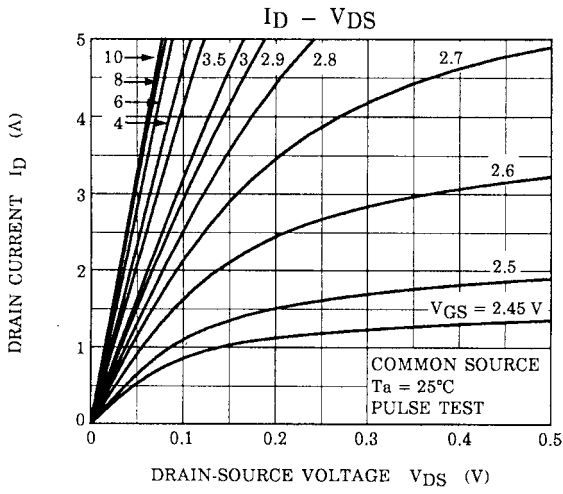


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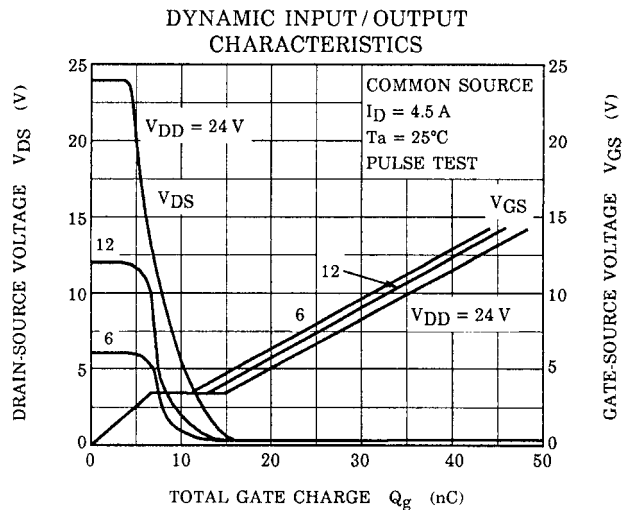
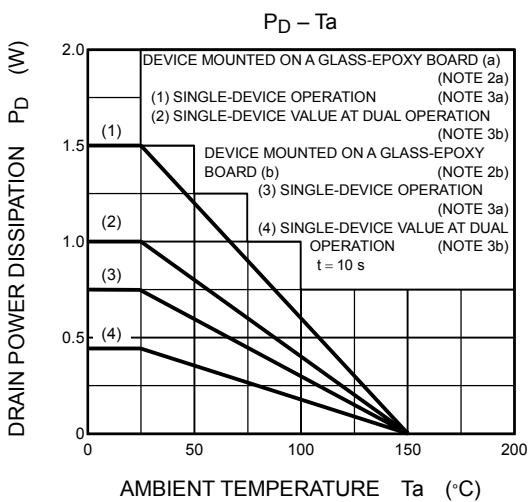
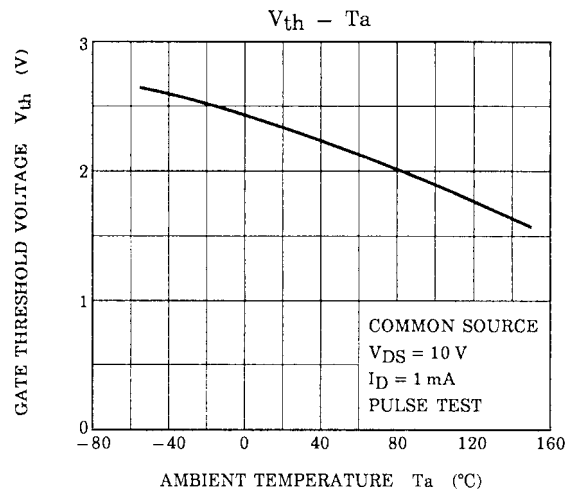
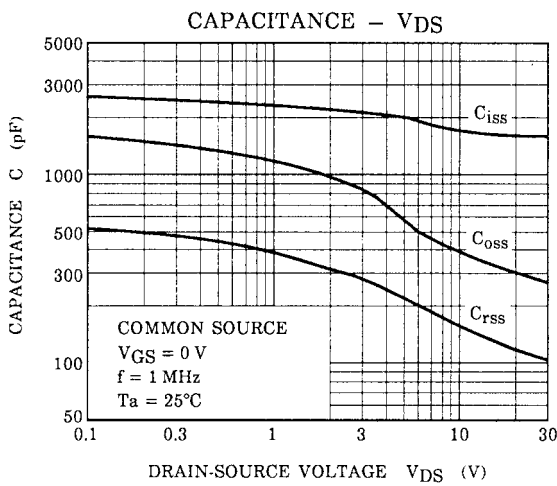
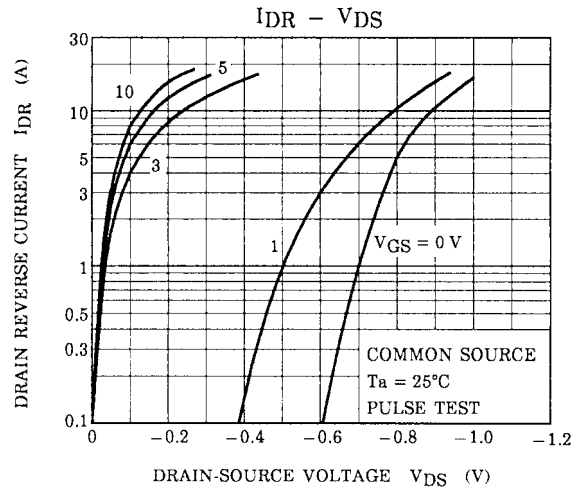
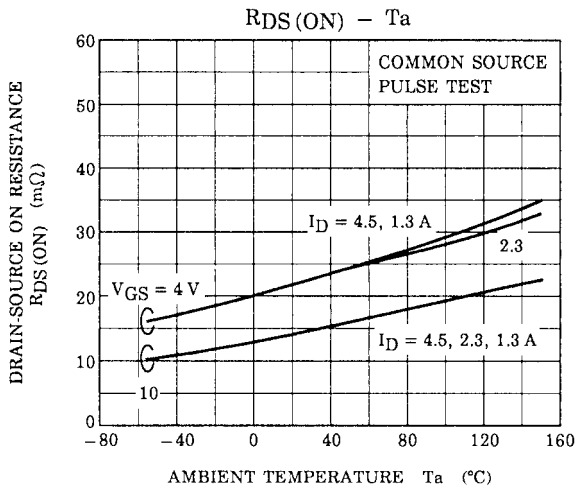


$T_{ch} = 25^\circ\text{C}$ (Initial)
 Peak $I_{AR} = -4.5\text{ A}$, $R_G = 25\ \Omega$, $V_{DD} = -24\text{ V}$, $L = 1.0\text{ mH}$
 $EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BV_{DSS}}{BV_{DSS} - V_{DD}} \right)$

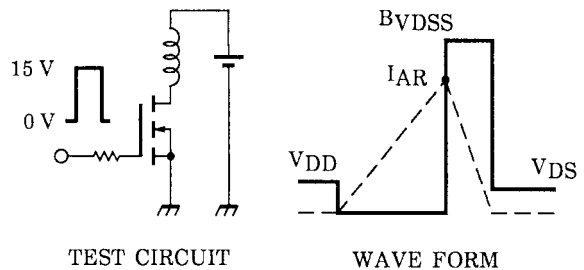
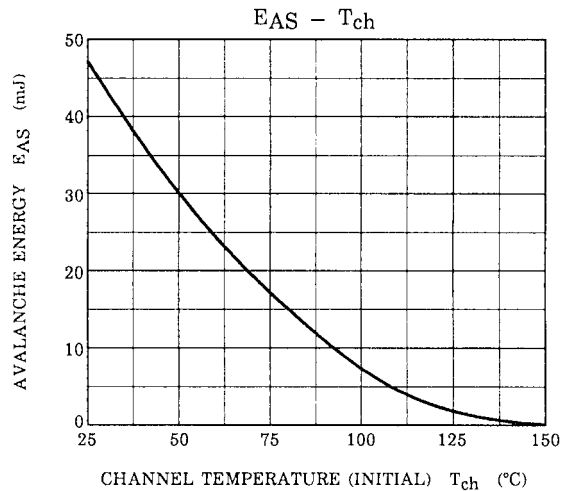
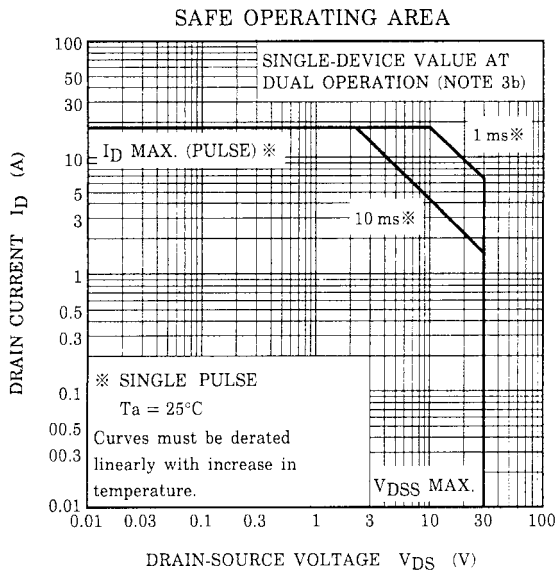
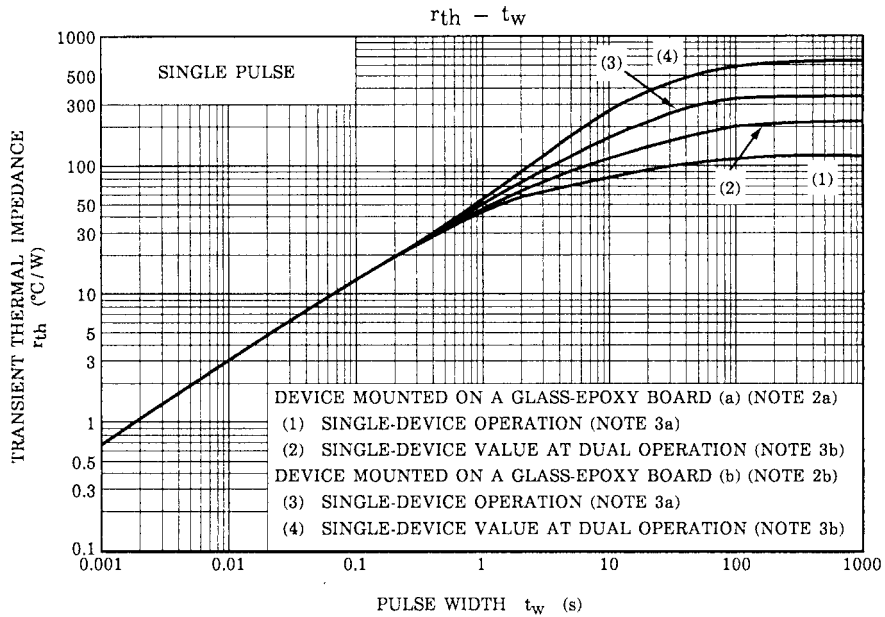
N-ch



N-ch



N-ch



$T_{ch} = 25^\circ\text{C}$ (Initial)
 Peak $I_{AR} = 6\text{ A}$, $R_G = 25\ \Omega$
 $V_{DD} = 24\text{ V}$, $L = 1.0\text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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